

ABSTRACT

A first system is provided that is configured to pattern a substrate that includes (1) a lithography subsystem configured to form a patterned masking layer on the substrate; and (2) an etch subsystem configured to receive the substrate after the patterned masking layer has been formed thereon and to etch the substrate to form one or more etched features on the substrate, the etch subsystem having an integrated inspection system configured to inspect the substrate; and (3) a controller coupled to the lithography subsystem and the etch subsystem. The controller includes computer program code configured to communicate with each subsystem and to perform the steps of receiving information about the substrate from the integrated inspection system of the etch subsystem; and adjusting a stepper focus of the lithography subsystem during formation of a subsequent patterned masking layer based at least in part on the information received from the etch subsystem.